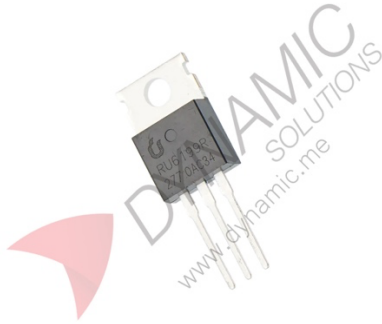


RU6199R N-Channel Power MOSFET IC



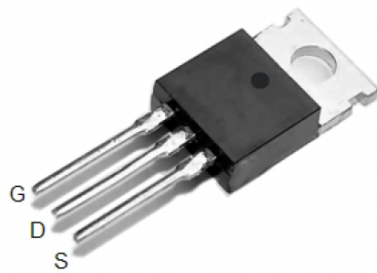
Features:

The RU6199R N-Channel Power MOSFET IC is an advanced power MOSFET designed for high current switching applications. It supports 60V drain-source voltage, 200A continuous drain current, low 2.8 mohm typical on-resistance at VGS=10V, avalanche energy rating, SMPS, and high speed power switching circuits.

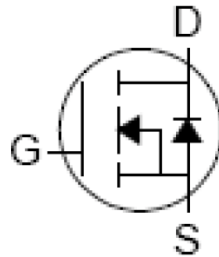
Specifications	
Part Number	RU6199R
Device Type	N-channel advanced power MOSFET IC
Drain-Source Voltage	60V
Gate-Source Voltage	+/-25V
Continuous Drain Current	200A at TC=25 deg C, 140A at TC=100 deg C
Pulsed Drain Current	800A
RDS(on)	2.8 mohm typical, 3.7 mohm maximum at VGS=10V, IDS=40A
Drain-Source Breakdown Voltage	60V minimum
Gate Threshold Voltage	2V minimum, 3V typical, 4V maximum
Zero Gate Voltage Drain Current	1uA maximum at VDS=60V, VGS=0V
Gate Leakage Current	+/-100nA maximum
Diode Forward Voltage	1.3V maximum
Reverse Recovery Time	75ns
Reverse Recovery Charge	150nC
Input Capacitance	5800pF
Output Capacitance	1500pF
Reverse Transfer Capacitance	490pF
Turn-On Delay Time	22ns
Turn-On Rise Time	38ns
Turn-Off Delay Time	75ns
Turn-Off Fall Time	120ns
Total Gate Charge	155nC
Gate-Source Charge	45nC
Gate-Drain Charge	48nC
Maximum Power Dissipation	300W at TC=25 deg C, 150W at TC=100 deg C
Thermal Resistance Junction to Case	0.5 deg C/W
Avalanche Energy Single Pulsed	1500mJ

Maximum Junction Temperature	175 deg C
Storage Temperature Range	-55 deg C to 175 deg C
Dimensions	3x1x0.4cm
Applications	Automotive applications, high efficiency synchronous SMPS, high speed power switching
Usage	High current power switching, power control, SMPS, and automotive electronic circuits

Pinouts:



TO-220



N-Channel MOSFET

Pin Name	Description
G	Gate controls the transistor channel and switches or adjusts current flow between drain and source
S	Source reference terminal where current exits the channel
D	Drain terminal where current enters the channel

Product Pictures:

